





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	2Ω @ $V_{GS} = 4.5V$	340mA
007	2.5Ω @ $V_{GS} = 2.5V$	300mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- **Power Management Functions**
- Backlighting

Features and Benefits

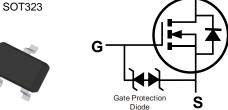
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

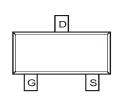
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)









Top View

Equivalent Circuit

Top View

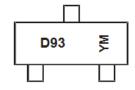
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN62D0UW-7	SOT323	3000/Tape & Reel
DMN62D0UW-13	SOT323	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D93= Product Type Marking Code YM or $\overline{Y}M = Date Code Marking$ Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

2010 0000 11	,											
Year	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	D	E	F	G	Н	ı	J	K	L	М	N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4	_	^	4	-	_	-7	0	^		N.I.	2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Steady $T_A = +25$ State $T_A = +70$			I _D	340 270	mA
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t<5s	$T_A = +25$ °C $T_A = +70$ °C	I _D	400 300	mA
Maximum Continuous Body Diode Forward Current	(Note 6)	Is	0.4	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 6)	I _{DM}	1.2	А	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	В	398	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	306	C/VV
Total Power Dissipation (Note 6)		P_{D}	470	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	273	°C/W
Thermal Resistance, Junction to Ambient (Note 0)	t<5s	$R_{\theta JA}$	235	C/VV
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

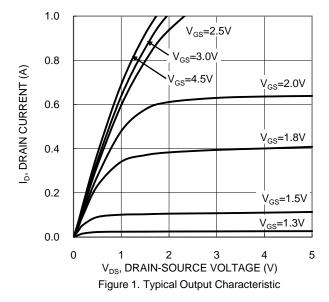
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.0	V	$V_{DS} = 10V, I_D = 250\mu A$	
			1.2	2.0		$V_{GS} = 4.5V, I_D = 0.1A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.4	2.5	Ω	$V_{GS} = 2.5V, I_D = 0.05A$	
			1.8	3.0		$V_{GS} = 1.8V, I_D = 0.05A$	
Forward Transconductance	Y _{fs}	_	1.8	_	S	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.3	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	32	_	pF	V 00V V 0V	
Output Capacitance	Coss	_	3.9	_	pF	$V_{DS} = 30V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	2.4	_	pF	1 = 1.000112	
Gate Resistance	Rq	_	101	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$	
Total Gate Charge	Qg	_	0.5	_	nC	451/1/ 401/	
Gate-Source Charge	Q _{qs}	_	0.09	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q_{qd}	_	0.09	_	nC	I _D = 250mA	
Turn-On Delay Time	t _{D(ON)}	_	2.4	_	ns		
Turn-On Rise Time	t _R	_	2.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	22.6	_	ns	$R_G = 25\Omega$, $I_D = 200mA$	
Turn-Off Fall Time	t _F	_	12.5	_	ns		

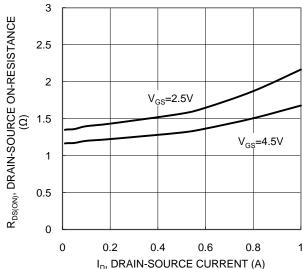
Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.









I_D, DRAIN-SOURCE CURRENT (A)
Figure 3. Typical On-Resistance vs. Drain Current and
Gate Voltage

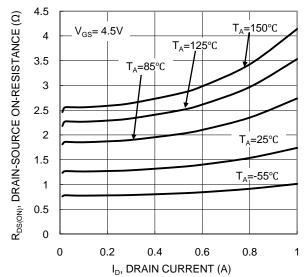
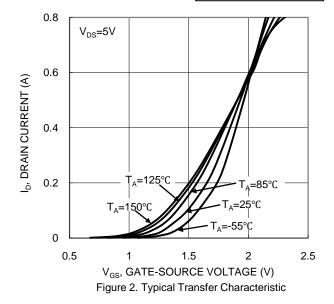
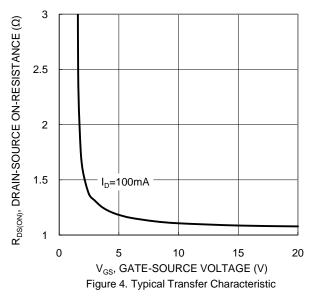


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





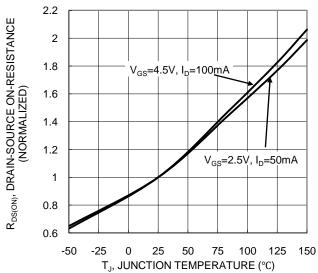
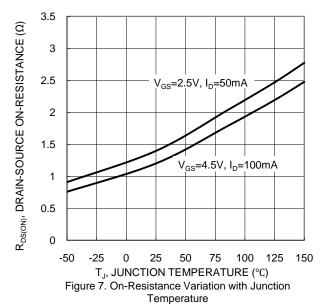
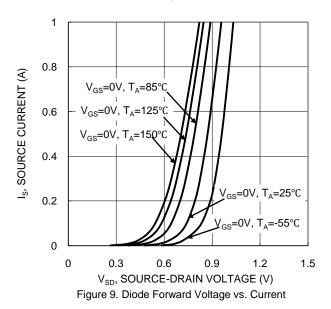


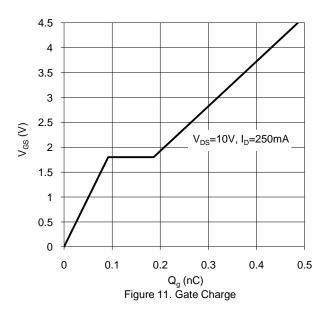
Figure 6. On-Resistance Variation with Junction Temperature

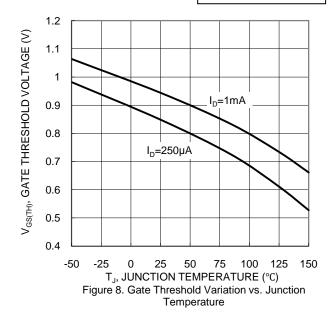


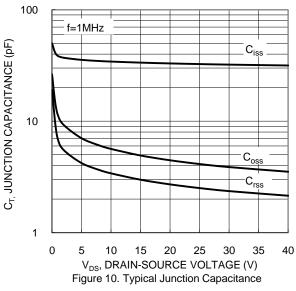


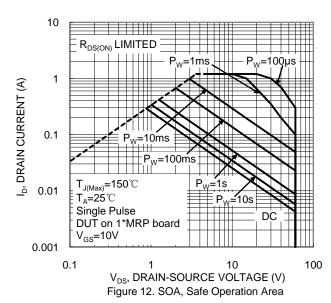






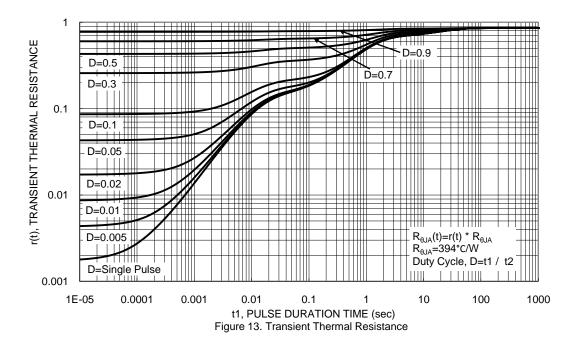






August 2016



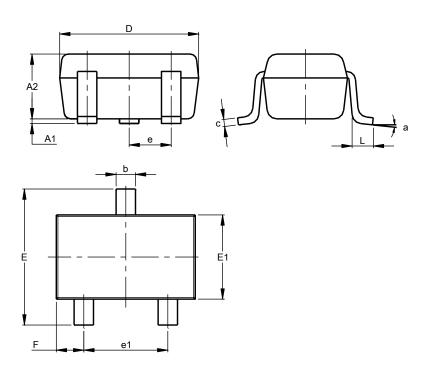




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323

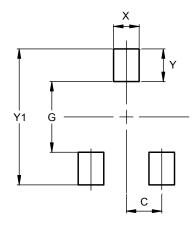


SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT323



Dimensions	Value
Dillicitatoria	(in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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